

C4D30120D–Silicon Carbide Schottky Diode

Z-REC™ RECTIFIER

V_{RRM}	=	1200 V
$I_F, T_C < 135^\circ\text{C}$	=	43 A
Q_c	=	192 nC

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

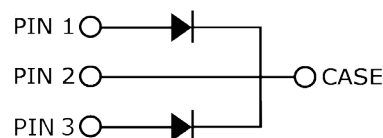
Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drives

Package



TO-247-3



Part Number	Package	Marking
C4D30120D	TO-247-3	C4D30120

Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_R	DC Peak Reverse Voltage	1200	V		
I_F	Continuous DC Current (Per Leg/Device)	21.5/43	A	$T_C=135^\circ\text{C}$, no AC component	
I_{FRM}	Repetitive Peak Forward Surge Current	68* 44*	A	$T_C=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_C=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	
I_{FSM}	Non-Repetitive Forward Surge Current	130* 117*	A	$T_C=25^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse $T_C=110^\circ\text{C}$, $t_p=10$ ms, Half Sine Pulse	
P_{tot}	Power Dissipation (Per Leg/Device)	220/440 95/190	W	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	
T_C	Maximum Case Temperature	135	$^\circ\text{C}$		
T_J	Operating Junction Range	-55 to +175	$^\circ\text{C}$		
T_{stg}	Storage Temperature Range	-55 to +135	$^\circ\text{C}$		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

** Per Device, * Per Leg

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.6 2.3	1.8 3	V	$I_F = 15\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 15\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	35 120	200 300	μA	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	96		nC	$V_R = 1200\text{ V}$, $I_F = 15\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	1200 70 50		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 800\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	

1. Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.34** 0.68*		$^\circ\text{C}/\text{W}$		

** Per Device, * Per Leg

Typical Performance (Per Leg)

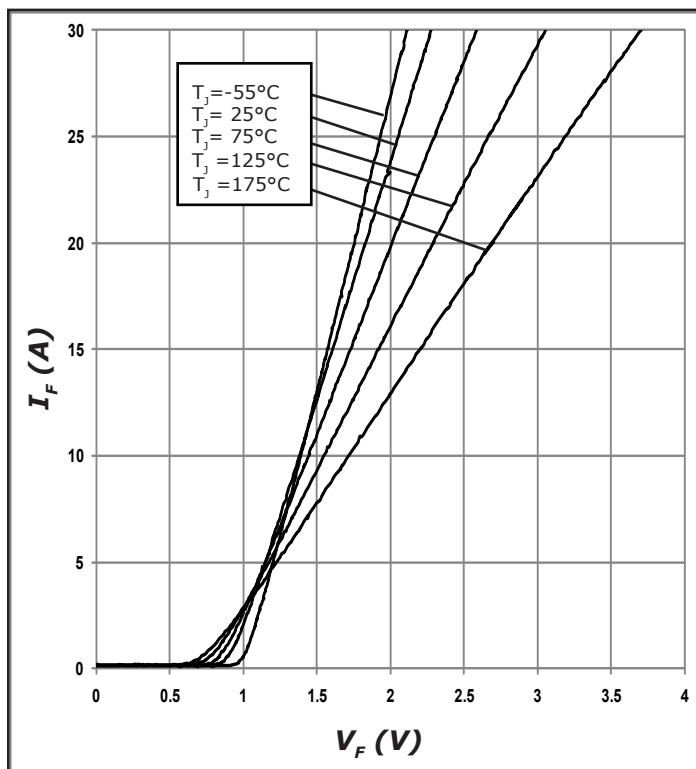


Figure 1. Forward Characteristics

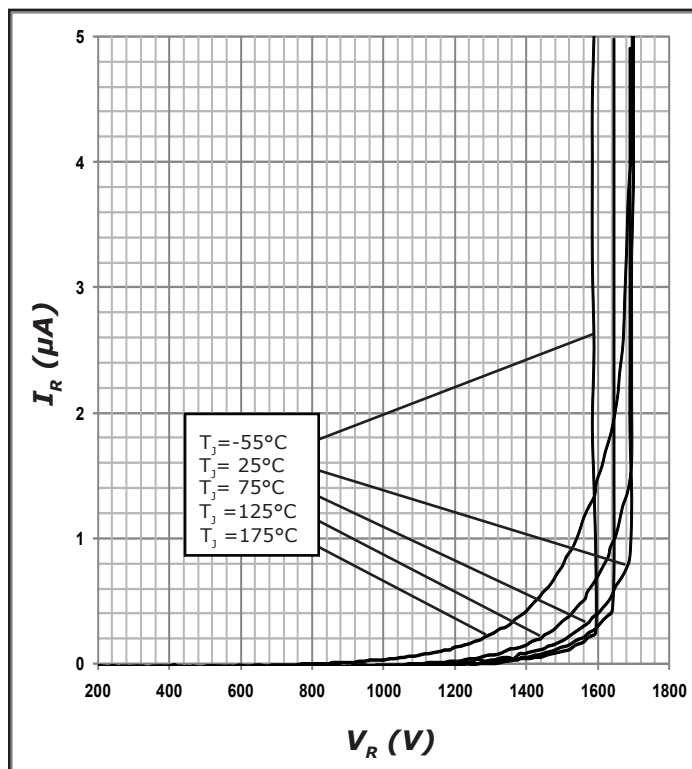


Figure 2. Reverse Characteristics

Typical Performance (Per Leg)

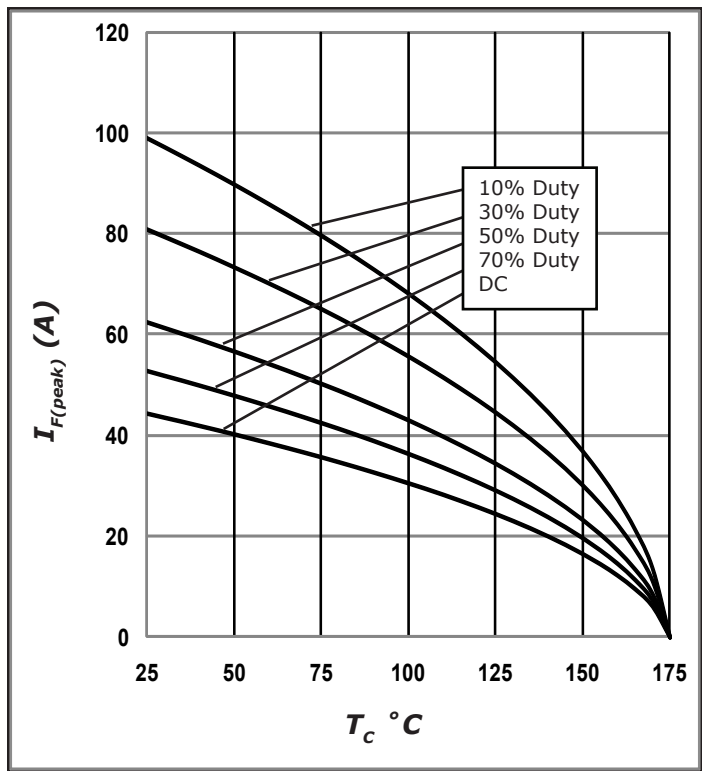


Figure 3. Current Derating

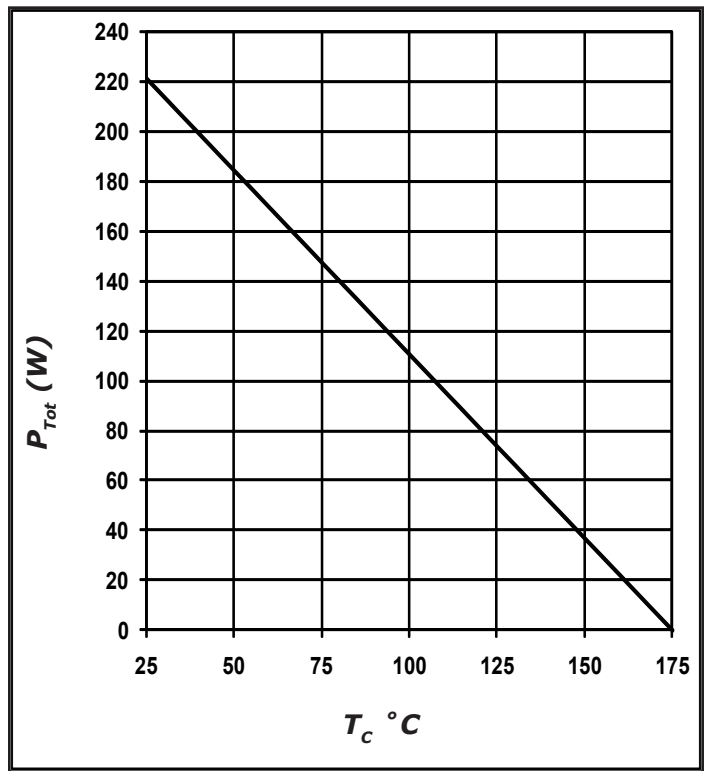


Figure 4. Power Derating

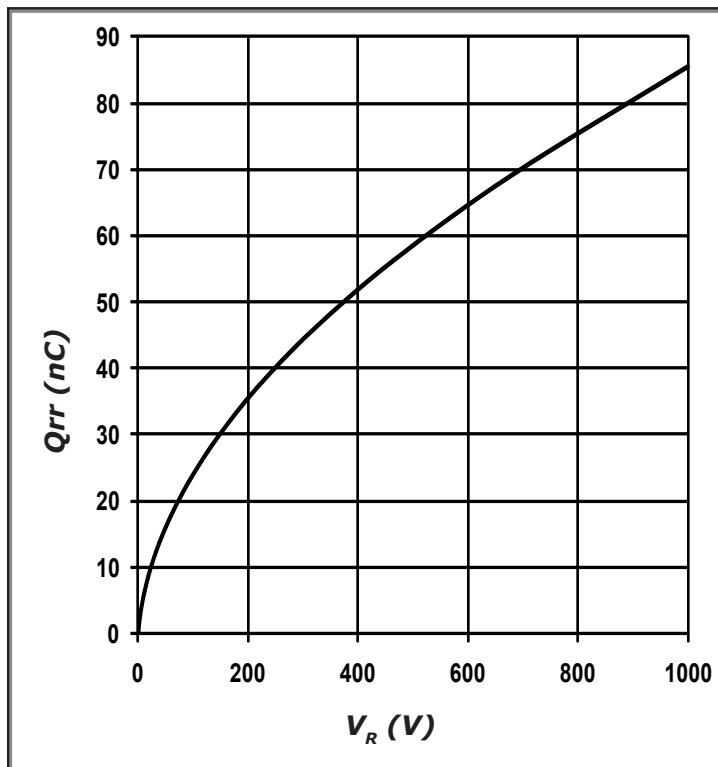


Figure 5. Recovery Charge vs. Reverse Voltage

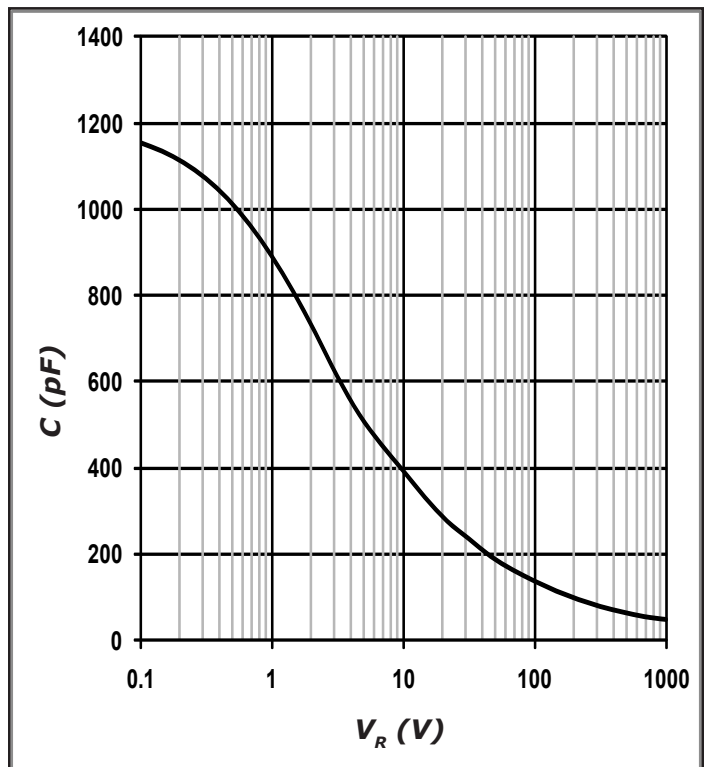


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance (Per Leg)

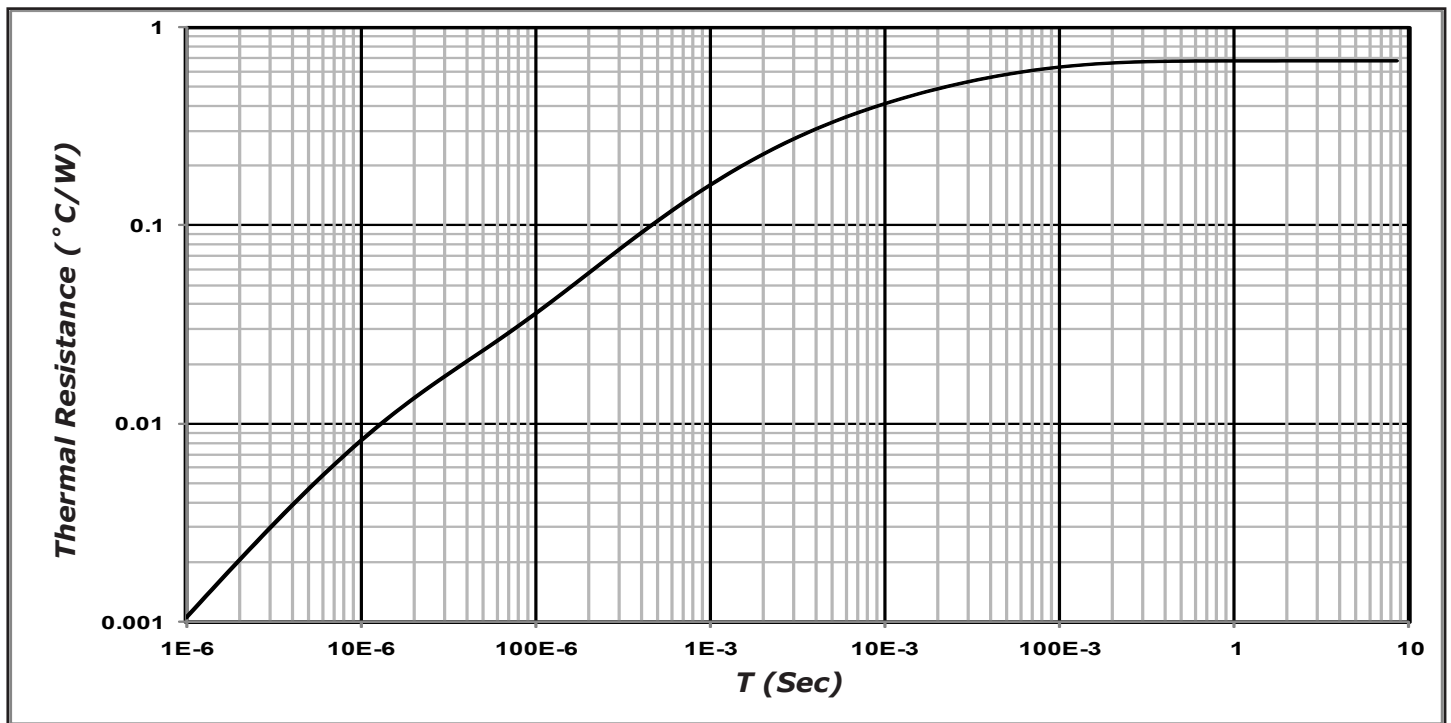
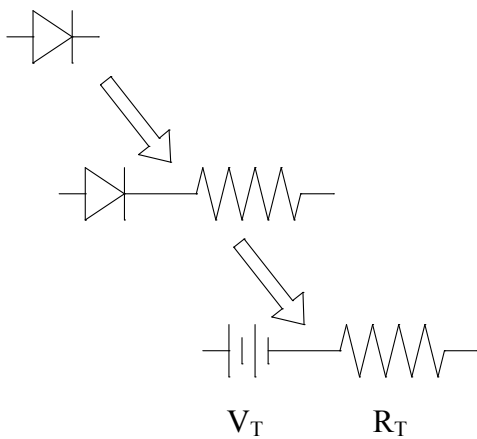


Figure 7. Transient Thermal Impedance

Diode Model



$$Vf_T = V_T + If * R_T$$

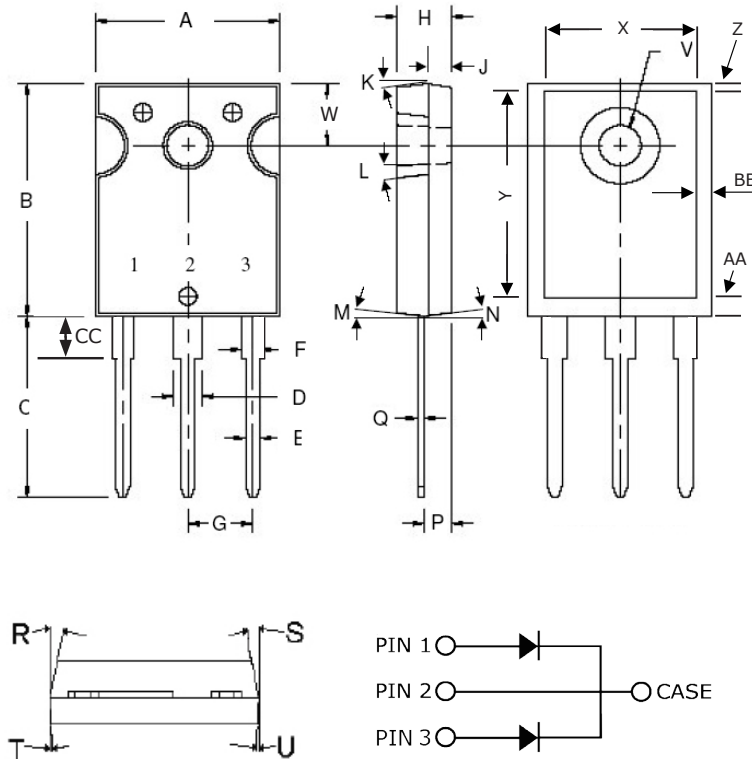
$$V_T = 0.97 + (T_j * -2.12 * 10^{-3})$$

$$R_T = 0.031 + (T_j * 3.92 * 10^{-4})$$

Note: T_j is diode junction temperature in degrees Celsius

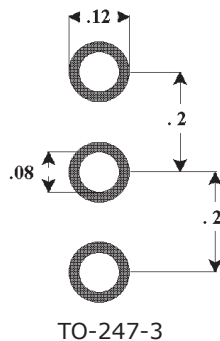
Package Dimensions

Package TO-247-3



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.605	.635	15.367	16.130
B	.800	.831	20.320	21.10
C	.780	.800	19.810	20.320
D	.095	.133	2.413	3.380
E	.046	.052	1.168	1.321
F	.060	.095	1.524	2.410
G	.215 TYP		5.460 TYP	
H	.175	.205	4.450	5.210
J	.075	.085	1.910	2.160
K	6°	21°	6°	21°
L	4°	6°	4°	6°
M	2°	4°	2°	4°
N	2°	4°	2°	4°
P	.090	.100	2.286	2.540
Q	.020	.030	.508	.762
R	9°	11°	9°	11°
S	9°	11°	9°	11°
T	2°	8°	2°	8°
U	2°	8°	2°	8°
V	.137	.144	3.487	3.658
W	.210	.248	5.334	6.300
X	.502	.557	12.751	14.150
Y	.637	.695	16.180	17.653
Z	.038	.052	0.964	1.321
AA	.110	.140	2.794	3.556
BB	.030	.046	0.766	1.168
CC	.161	.176	4.100	4.472

Recommended Solder Pad Layout



Part Number	Package	Marking
C4D30120D	TO-247-3	C4D30120

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